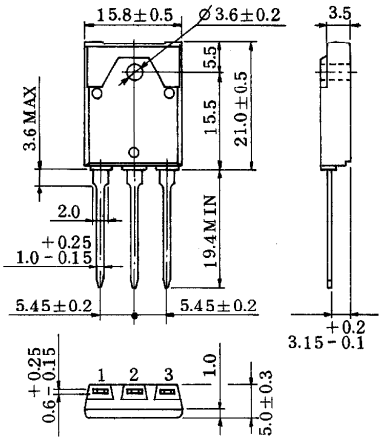
TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

2SA1803

POWER AMPLIFIER APPLICATIONS

Unit in mm

- Complementary to 2SC4688
- Recommend for 40W High Fidelity Audio Frequency Amplifier output Stage.



1. BASE
2. COLLECTOR
3. EMITTER

JEDEC	—
EIAJ	—
TOSHIBA	2-16F1A

Weight : 5.8g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	−80	V
Collector-Emitter Voltage		V_{CEO}	−80	V
Emitter-Base Voltage		V_{EBO}	−5	V
Collector Current	DC	I_C	−6	A
	Pulse	I_{CP}	−12	
Base Current		I_B	−0.6	A
Collector Power Dissipation (Tc = 25°C)		P_C	55	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} = −80V, I_E = 0	—	—	−5.0	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} = −5V, I_C = 0	—	—	−5.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = −50mA, I_B = 0	−80	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	V_{CE} = −5V, I_C = −1A	55	—	160	
	$h_{FE(2)}$	V_{CE} = −5V, I_C = −3A	35	80	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = −5A, I_B = −0.5A	—	−1.0	−2.0	V
Base-Emitter Voltage	V_{BE}	V_{CE} = −5V, I_C = −3A	—	−0.95	−1.5	V
Transition Frequency	f_T	V_{CE} = −5V, I_C = −1A	—	30	—	MHz
Collector Output Capacitance	C_{ob}	V_{CB} = −10V, I_E = 0, f = 1MHz	—	290	—	pF

Note : $h_{FE(1)}$ Classification R : 55~110, O : 80~160

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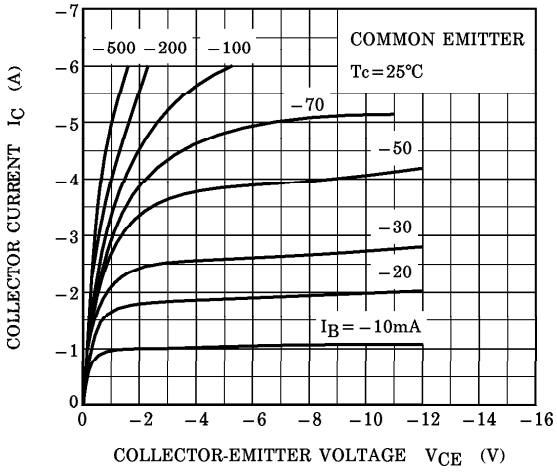
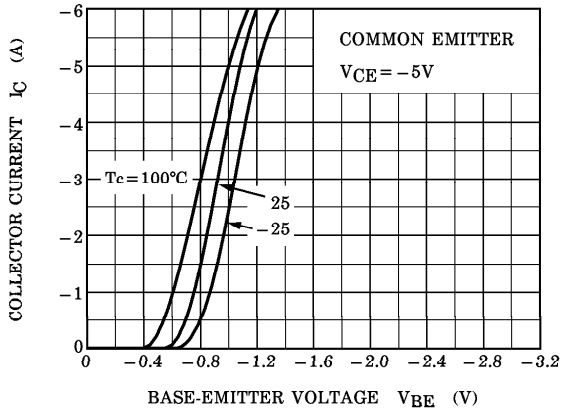
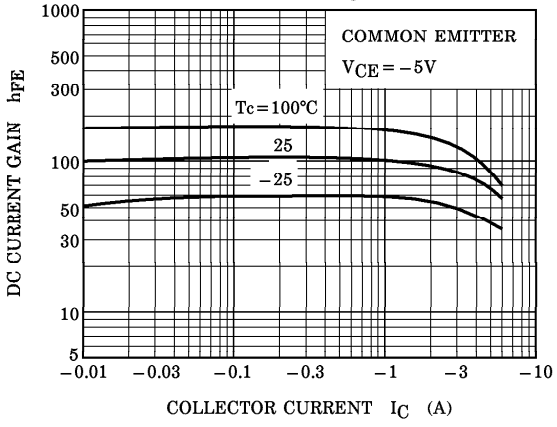
I_C – V_{CE}



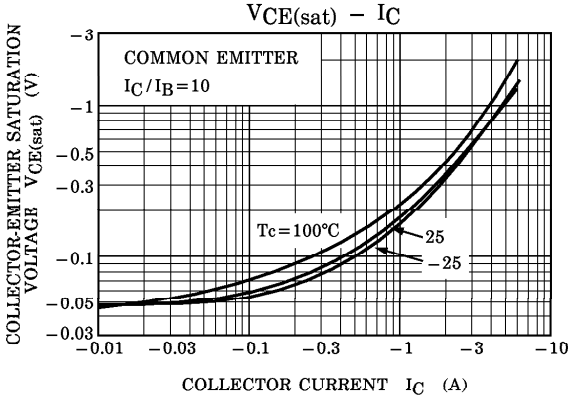
I_C – V_{BE}



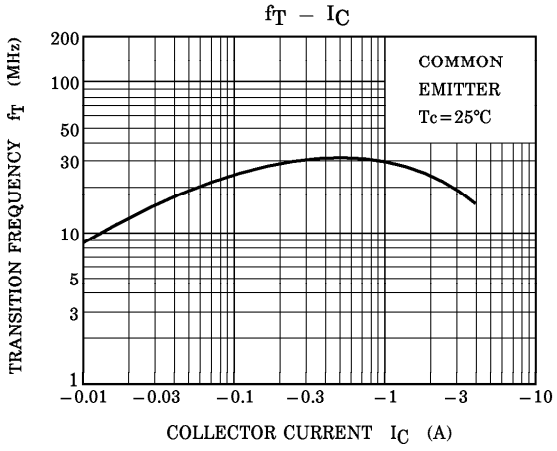
h_{FE} – I_C



$V_{CE(sat)}$ – I_C



f_T – I_C



SAFE OPERATING AREA